

# **Excellent Integrated System Limited**

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

<u>Vishay Semiconductor/Diodes Division</u> <u>VS-10CDH06-M3/I</u>

For any questions, you can email us directly: <a href="mailto:sales@integrated-circuit.com">sales@integrated-circuit.com</a>

Datasheet of VS-10CDH06-M3/I - DIODE GP 600V 2X5A TO-263AC

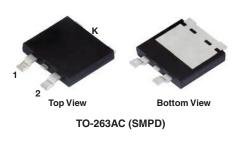
Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

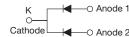


#### VS-10CDH06-M3

Vishay Semiconductors

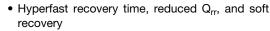
# Hyperfast Rectifier, 2 x 5 A FRED Pt®





PRODUCT SUMMARY				
Package	TO-263AC (SMPD)			
I <sub>F(AV)</sub>	2 x 5 A			
$V_{R}$	600 V			
V <sub>F</sub> at I <sub>F</sub>	1 V			
t <sub>rr</sub>	35 ns			
T <sub>J</sub> max.	175 °C			
Diode variation	Dual die			

#### **FEATURES**





175 °C maximum operating junction temperature

• For PFC CRM / CCM, snubber operation

RoH

Low forward voltage drop

COMPLIANT HALOGEN

· Low leakage current

 Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

• Meets JESD 201 class 2 whisker test

 Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in PFC, boost, in the AC/DC section of SMPS, freewheeling and clamp diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage		$V_{RRM}$		600	V
A	per device	I <sub>F(AV)</sub>	T <sub>solder pad</sub> = 153 °C	10	
Average rectified forward current	per diode			5	۸
New yearstitive most surrous surrous	per device	1	T <sub>J</sub> = 25 °C, 6 ms square pulse	110	А
Non-repetitive peak surge current	per diode	IFSM		60	

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_{BR}$ , $V_{R}$	I <sub>R</sub> = 100 μA	600	-	-	
Forward voltage, per diode V <sub>F</sub>	M	I <sub>F</sub> = 5 A	-	1.2	1.5	V
	I <sub>F</sub> = 5 A, T <sub>J</sub> = 150 °C	-	1	1.25		
David and the latest and the design of the d	1	V <sub>R</sub> = V <sub>R</sub> rated	-	-	3	
Reverse leakage current, per diode I <sub>R</sub>		T <sub>J</sub> = 150 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	15	150	μΑ
Junction capacitance, per diode	C <sub>T</sub>	V <sub>R</sub> = 600 V	-	6	-	pF

Revision: 10-Feb-15 Document Number: 95808

Datasheet of VS-10CDH06-M3/I - DIODE GP 600V 2X5A TO-263AC





#### VS-10CDH06-M3

### Vishay Semiconductors

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST C	ONDITIONS	MIN.	TYP.	MAX.	UNITS
		I <sub>F</sub> = 1 A, dI <sub>F</sub> /dt = 50	A/μs, V <sub>R</sub> = 30 V	-	35	-	
Deverage receivers times		I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1 A, I <sub>rr</sub> = 0.25 A		-	-	35	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	45	-	ns
		T <sub>J</sub> = 125 °C		-	70	-	
Dook roopyony gurrent	1	T <sub>J</sub> = 25 °C	$I_F = 5 A,$ $dI_F/dt = 500 A/\mu s,$ $V_R = 400 V$	-	7	-	۸
Peak recovery current	IRRM	T <sub>J</sub> = 125 °C		-	10	-	A
Deviana nacevani abance	everse recovery charge Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	160	-	C
neverse recovery charge		T <sub>J</sub> = 125 °C	7	-	370	-	nC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	+175	°C
Thermal resistance, per diode junction to solder pad	R <sub>thJ-Sp</sub>		-	2.4	3.3	°C/W
Approximate weight				0.55		g
Approximate weight				0.02		oz.
Marking device		Case style TO-263AC (SMPD)		10CI	DH06	

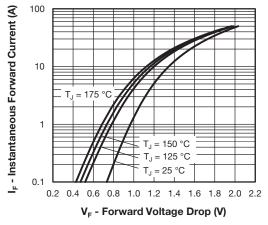


Fig. 1 - Typical Forward Voltage Drop Characteristics

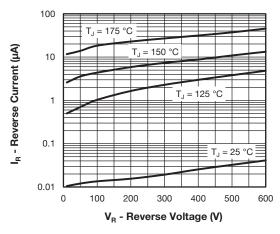


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

#### VS-10CDH06-M3

#### Vishay Semiconductors

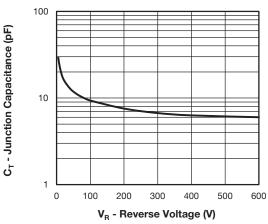


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

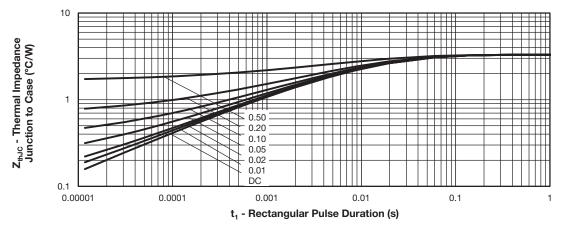


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

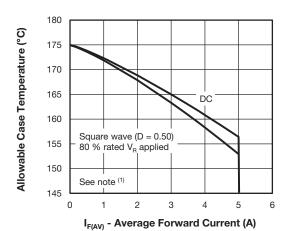


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

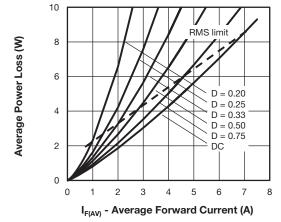


Fig. 6 - Forward Power Loss Characteristics

#### Note

 $^{(1)}$  Formula used:  $T_C = T_J$  - (Pd + Pd\_{REV}) x R<sub>thJC</sub>; Pd = Forward power loss = I<sub>F(AV)</sub> x V<sub>FM</sub> at (I<sub>F(AV)</sub>/D) (see fig. 5); Pd<sub>REV</sub> = Inverse power loss = V<sub>R1</sub> x I<sub>R</sub> (1 - D); I<sub>R</sub> at V<sub>R1</sub> = rated V<sub>R</sub>

Revision: 10-Feb-15 3 Document Number: 95808

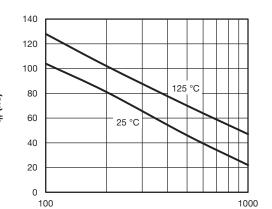
Datasheet of VS-10CDH06-M3/I - DIODE GP 600V 2X5A TO-263AC

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

#### VS-10CDH06-M3

# VISHAY.

#### www.vishay.com



 $\label{eq:dI_F} dI_F/dt~\text{(A/$\mu$s)}$  Fig. 7 - Typical Reverse Recovery Time vs.  $dI_F/dt$ 

# Vishay Semiconductors

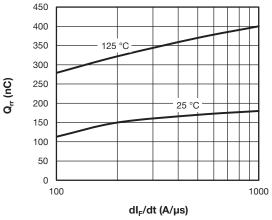
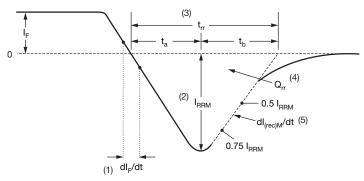


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt



- (1) dI<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  ${\rm Q_{rr}}$  area under curve defined by  ${\rm t_{rr}}$  and  ${\rm I_{RRM}}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 9 - Reverse Recovery Waveform and Definitions

Datasheet of VS-10CDH06-M3/I - DIODE GP 600V 2X5A TO-263AC

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

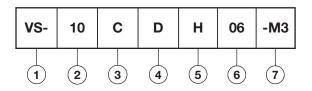


#### VS-10CDH06-M3

#### Vishay Semiconductors

#### **ORDERING INFORMATION TABLE**

**Device code** 



- 1 Vishay Semiconductors product
- Current rating (10 A)
- 3 Circuit configuration:
  - C = common cathode
- D = SMPD package
- 5 Process type,
  - H = hyperfast recovery
- 6 Voltage code (06 = 600 V)
- 7 M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION				
VS-10CDH06-M3/I	2000	2000	13" diameter plastic tape and reel		

LINKS TO RELATED DOCUMENTS		
Dimensions <u>www.vishay.com/doc?95604</u>		
Part marking information	www.vishay.com/doc?95566	
Packaging information	www.vishay.com/doc?88869	



Datasheet of VS-10CDH06-M3/I - DIODE GP 600V 2X5A TO-263AC

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



# **Legal Disclaimer Notice**

Vishay

#### **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Revision: 13-Jun-16 1 Document Number: 91000